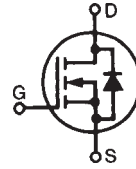


MegaMOS™ FET

IXTH / IXTM 67N10
 IXTH / IXTM 75N10
 IXTT 75N10

V _{DSS}	I _{D25}	R _{DS(on)}
100 V	67 A	25 mΩ
100 V	75 A	20 mΩ

N-Channel Enhancement Mode



Symbol	Test Conditions	Maximum Ratings	
V _{DSS}	T _J = 25°C to 150°C	100	V
V _{DGR}	T _J = 25°C to 150°C; R _{GS} = 1 MΩ	100	V
V _{GS}	Continuous	±20	V
V _{GSM}	Transient	±30	V
I _{D25}	T _C = 25°C	67N10 75N10	67 75 A
I _{DM}	T _C = 25°C, pulse width limited by T _{JM}	67N10 75N10	268 300 A
P _D	T _C = 25°C	300	W
T _J		-55 ... +150	°C
T _{JM}		150	°C
T _{stg}		-55 ... +150	°C
M _d	Mounting torque	1.13/10	Nm/lb.in.
Weight		TO-204	18 g
		TO-247	6 g
		TO-268	5 g
Maximum lead temperature for soldering 1.6 mm (0.062 in.) from case for 10 s		10	°C

TO-247 AD (IXTH)

TO-204 AE (IXTM)

TO-268 (IXTT)

G = Gate, D = Drain,
 S = Source, TAB = Drain

Features

- International standard packages
- Low R_{DS(on)} HDMOS™ process
- Rugged polysilicon gate cell structure
- Unclamped Inductive Switching (UIS) rated
- Low package inductance
 - easy to drive and to protect
- Fast intrinsic Rectifier

Applications

- DC-DC converters
- Synchronous rectification
- Battery chargers
- Switched-mode and resonant-mode power supplies
- DC choppers
- AC motor control
- Temperature and lighting controls
- Low voltage relays

Advantages

- Easy to mount with 1 screw (TO-247) (isolated mounting screw hole)
- Space savings
- High power density

Symbol	Test Conditions	Characteristic Values (T _J = 25°C, unless otherwise specified)		
		min.	typ.	max.
V _{DSS}	V _{GS} = 0 V, I _D = 250 μA	100		V
V _{GS(th)}	V _{DS} = V _{GS} , I _D = 4 mA	2.0		V
I _{GSS}	V _{GS} = ±20 V _{DC} , V _{DS} = 0			±100 nA
I _{DSS}	V _{DS} = 0.8 • V _{DSS} V _{GS} = 0 V	T _J = 25°C		250 μA
		T _J = 125°C		1 mA
R _{DS(on)}	V _{GS} = 10 V, I _D = 0.5 I _{D25} Pulse test, t ≤ 300 μs, duty cycle d ≤ 2 %	67N10		0.025 Ω
		75N10		0.020 Ω

IXYS reserves the right to change limits, test conditions, and dimensions.

DS91533F(9/03)

Symbol	Test Conditions	Characteristic Values ($T_J = 25^\circ\text{C}$, unless otherwise specified)			
		min.	typ.	max.	
g_{fs}	$V_{DS} = 10\text{ V}; I_D = I_{D25}$, pulse test	25	30	S	
C_{iss}	$V_{GS} = 0\text{ V}, V_{DS} = 25\text{ V}, f = 1\text{ MHz}$		4500	pF	
C_{oss}			1300	pF	
C_{rss}			550	pF	
$t_{d(on)}$	$V_{GS} = 10\text{ V}, V_{DS} = 0.5 \cdot V_{DSS}, I_D = 0.5 I_{D25}$ $R_G = 2\ \Omega$, (External)		40	60	ns
t_r			60	110	ns
$t_{d(off)}$			100	140	ns
t_f			30	60	ns
$Q_{g(on)}$	$V_{GS} = 10\text{ V}, V_{DS} = 0.5 \cdot V_{DSS}, I_D = 0.5 I_{D25}$		180	260	nC
Q_{gs}			30	70	nC
Q_{gd}			90	160	nC
R_{thJC}	(TO-204, TO-247)			0.42	K/W
R_{thCK}			0.25		K/W

Source-Drain Diode

Symbol	Test Conditions	Characteristic Values ($T_J = 25^\circ\text{C}$, unless otherwise specified)			
		min.	typ.	max.	
I_S	$V_{GS} = 0\text{ V}$	67N10 75N10		67 75	A A
I_{SM}	Repetitive; pulse width limited by T_{JM}	67N10 75N10		268 300	A A
V_{SD}	$I_F = I_S, V_{GS} = 0\text{ V}$, Pulse test, $t \leq 300\ \mu\text{s}$, duty cycle $d \leq 2\%$			1.75	V
t_{rr}	$I_F = I_S, -di/dt = 100\text{ A}/\mu\text{s}, V_R = 100\text{ V}$		200		ns

TO-247 AD (IXTH) Outline

Terminals: 1 - Gate 2 - Drain
3 - Source Tab - Drain

Dim.	Millimeter		Inches	
	Min.	Max.	Min.	Max.
A	4.7	5.3	.185	.209
A ₁	2.2	2.54	.087	.102
A ₂	2.2	2.6	.059	.098
b	1.0	1.4	.040	.055
b ₁	1.65	2.13	.065	.084
b ₂	2.87	3.12	.113	.123
C	.4	.8	.016	.031
D	20.80	21.46	.819	.845
E	15.75	16.26	.610	.640
e	5.20	5.72	0.205	0.225
L	19.81	20.32	.780	.800
L ₁		4.50		.177
ØP	3.55	3.65	.140	.144
Q	5.89	6.40	0.232	0.252
R	4.32	5.49	.170	.216
S	6.15	BSC	242	BSC

TO-204AE (IXTM) Outline

Pins 1 - Gate 2 - Source
Case - Drain

Dim.	Millimeter		Inches	
	Min.	Max.	Min.	Max.
A	6.4	11.4	.250	.450
A ₁		3.42		.135
Øb	.97	1.09	.038	.043
ØD		22.22		.875
e	10.67	11.17	.420	.440
e ₁	5.21	5.71	.205	.225
L	7.93		.312	
Øp	3.84	4.19	.151	.165
Øp ₁	3.84	4.19	.151	.165
q	30.15	BSC	1.187	BSC
R		13.33		.525
R ₁		4.77		.188
s	16.64	17.14	.655	.675

TO-268 (IXTT) Outline

SYM	INCHES		MILLIMETERS	
	MIN	MAX	MIN	MAX
A	.193	.201	4.90	5.10
A ₁	.106	.114	2.70	2.90
A ₂	.001	.010	0.02	0.25
b	.045	.057	1.15	1.45
b ₂	.075	.083	1.90	2.10
C	.016	.026	0.40	0.65
C ₂	.057	.063	1.45	1.60
D	.543	.551	13.80	14.00
D ₁	.488	.500	12.40	12.70
E	.624	.632	15.85	16.05
E ₁	.524	.535	13.30	13.60
e	.215 BSC		5.45 BSC	
H	.736	.752	18.70	19.10
L	.094	.106	2.40	2.70
L ₁	.047	.055	1.20	1.40
L ₂	.039	.045	1.00	1.15
L ₃	.010	BSC	0.25	BSC
L ₄	.150	.161	3.80	4.10

Fig. 1 Output Characteristics

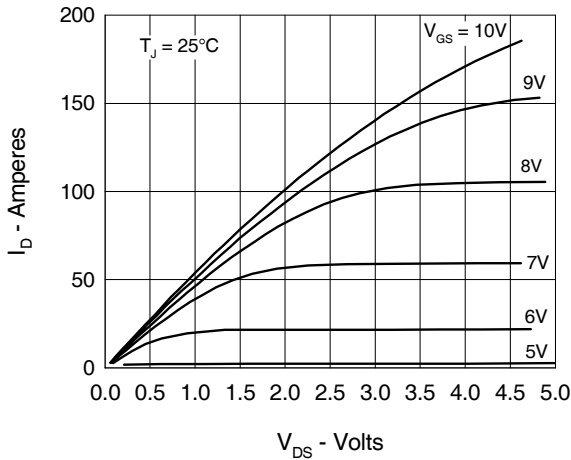


Fig. 2 Input Admittance

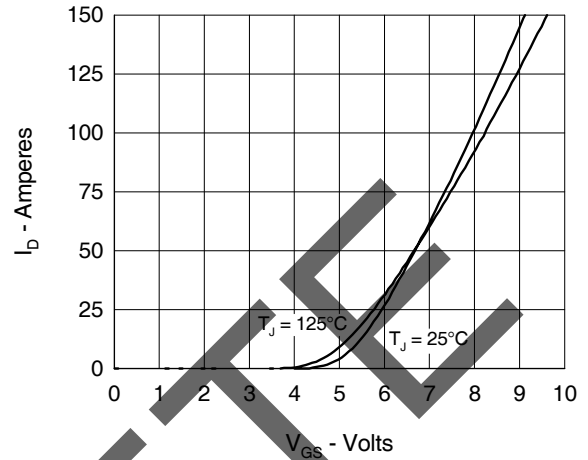


Fig. 3 $R_{DS(on)}$ vs. Drain Current

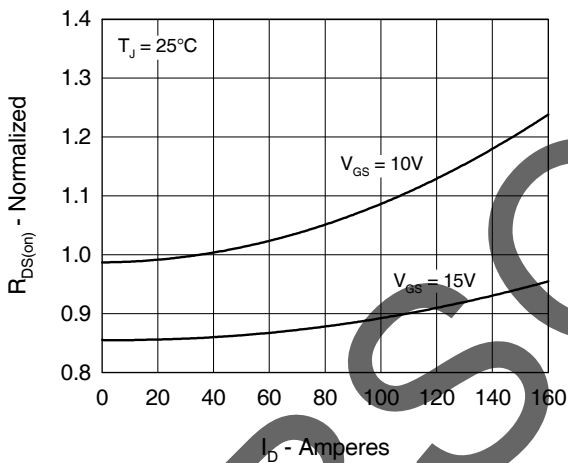


Fig. 4 Temperature Dependence of Drain to Source Resistance

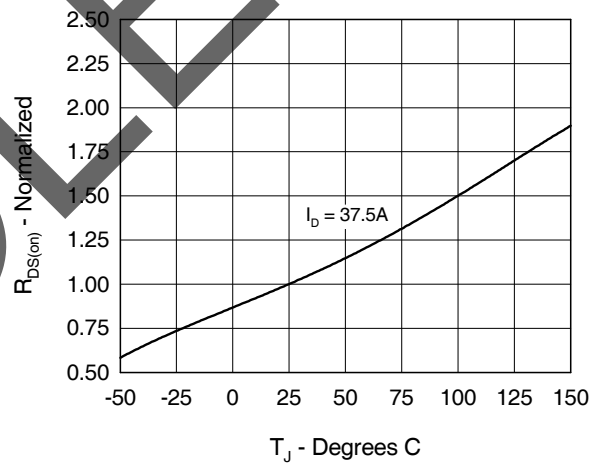


Fig. 5 Drain Current vs. Case Temperature

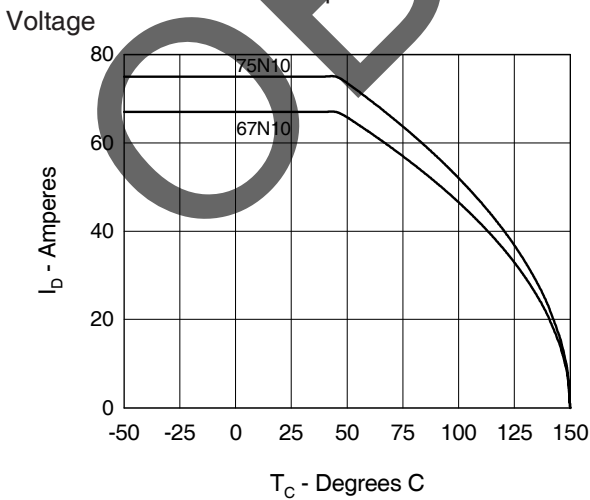


Fig. 6 Temperature Dependence of Breakdown and Threshold

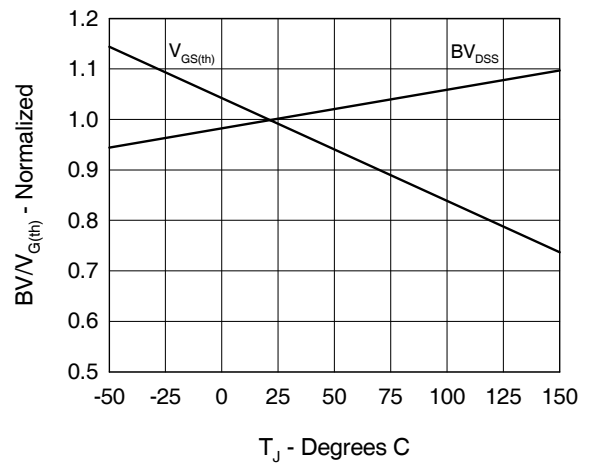


Fig.7 Gate Charge Characteristic Curve

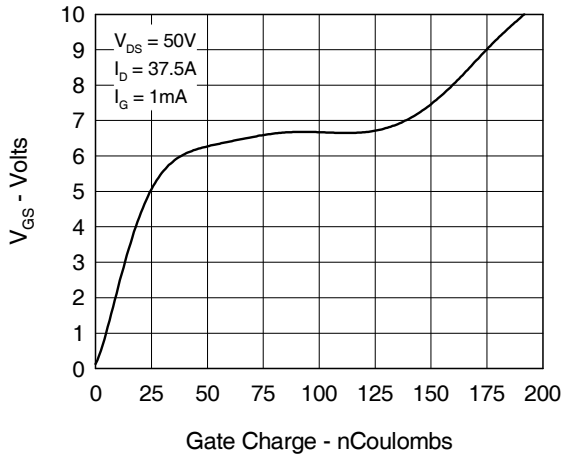


Fig.9 Capacitance Curves

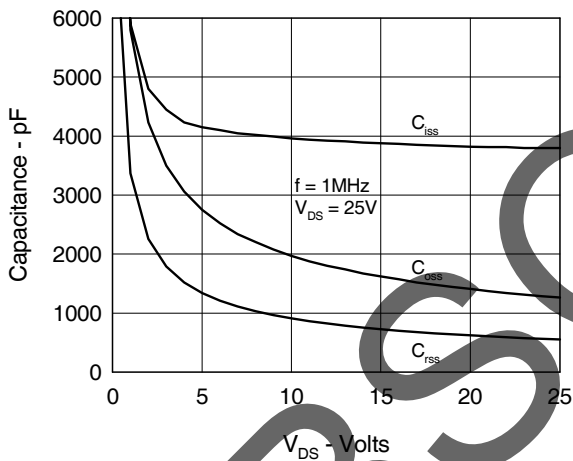


Fig.11 Transient Thermal Impedance

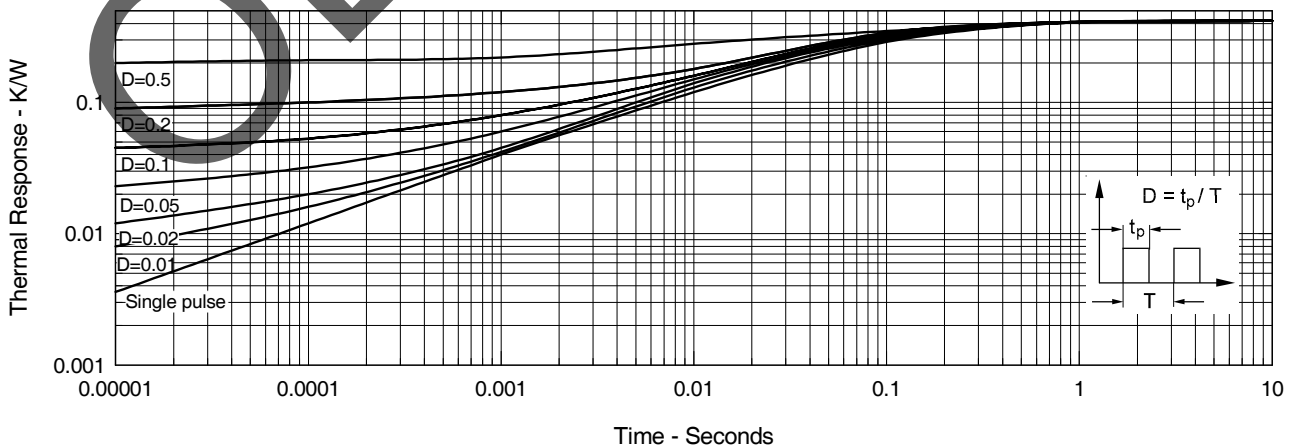


Fig.8 Forward Bias Safe Operating Area

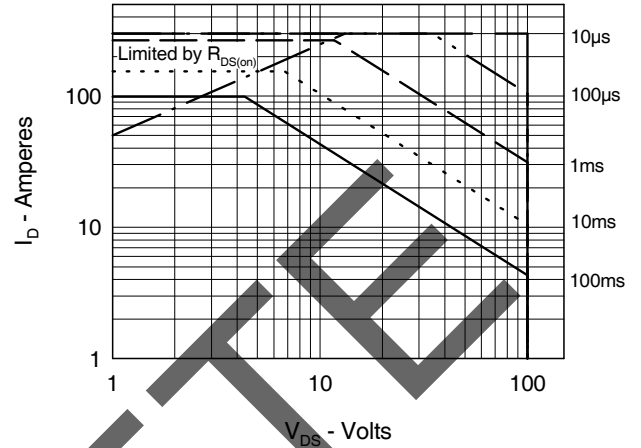
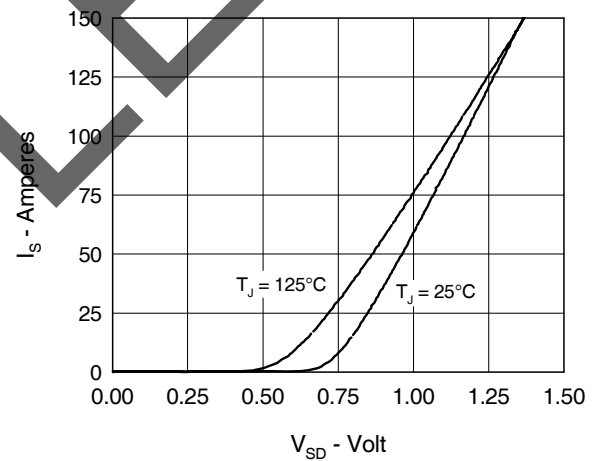


Fig.10 Source Current vs. Source to Drain Voltage





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